



HIGH VOLTAGE SILICON RECTIFIERS

- SMALL SIZE MOLDED PACKAGE
- PRV 15,000 TO 30,000 VOLTS
- FAST RECOVERY
- AVALANCHE CHARACTERISTICS
- LOW LEAKAGE



EDI Type	PRV (Volts)	REVERSE RECOVERY TIME IN NANoseconds @25 °C (Fig.4)	MAXIMUM FORWARD VOLTAGE DROP @25mA
CRVT 150	15,000	100	35 Volts
CRVT 200	20,000	100	35 Volts
CRVT 250	25,000	100	35 Volts
CRVT 300	30,000	100	48 Volts

ELECTRICAL CHARACTERISTICS (at T_A=25 °C Unless Otherwise Specified)

Average Rectified Forward Current @ 75°C, (Fig.1)	25 mA
Max Peak Surge Current (8.3ms) (Fig.2)	3 Amp
Max DC Reverse Current @ PRV and 25°C	1 μA
Max DC Reverse Current @ PRV and 100 °C	25 μA
Ambient Operating Temperature Range	-55°C to +125 °C
Storage Temperature Range	-55°C to +150 °C

NOTES:

- 1.It is recommended that a proper heat sink be used on the terminals of this device between the body and soldering point to prevent damage from excess heat.
- 2.If operated over 10,000v/inch in length, devices should be immersed in oil or re - encapsulated.

EDI reserves the right to change these specifications at any time without notice.

FIG.1

OUTPUT CURRENT vs AMBIENT TEMPERATURE

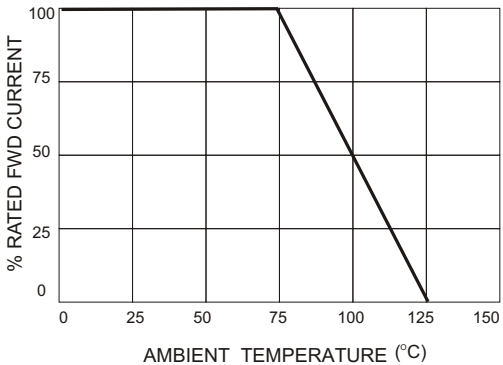


FIG.2

NON-REPETITIVE SURGE CURRENT

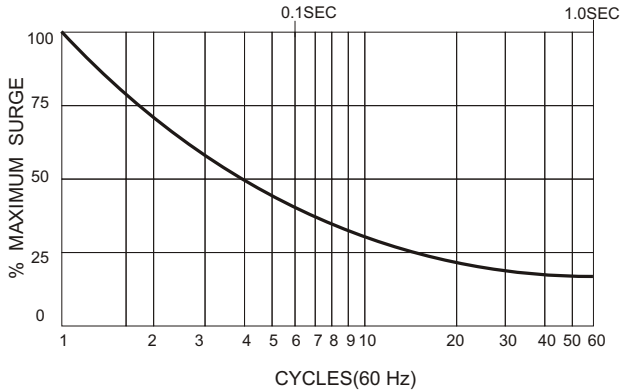


FIG.3

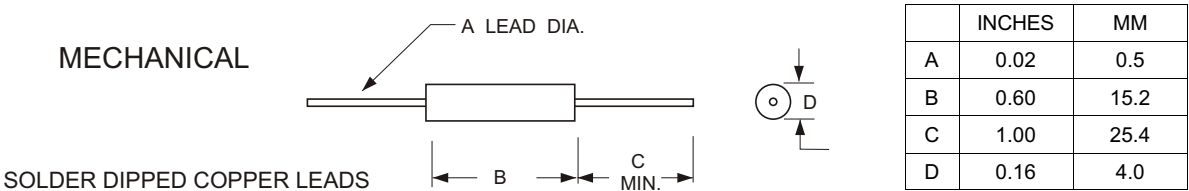
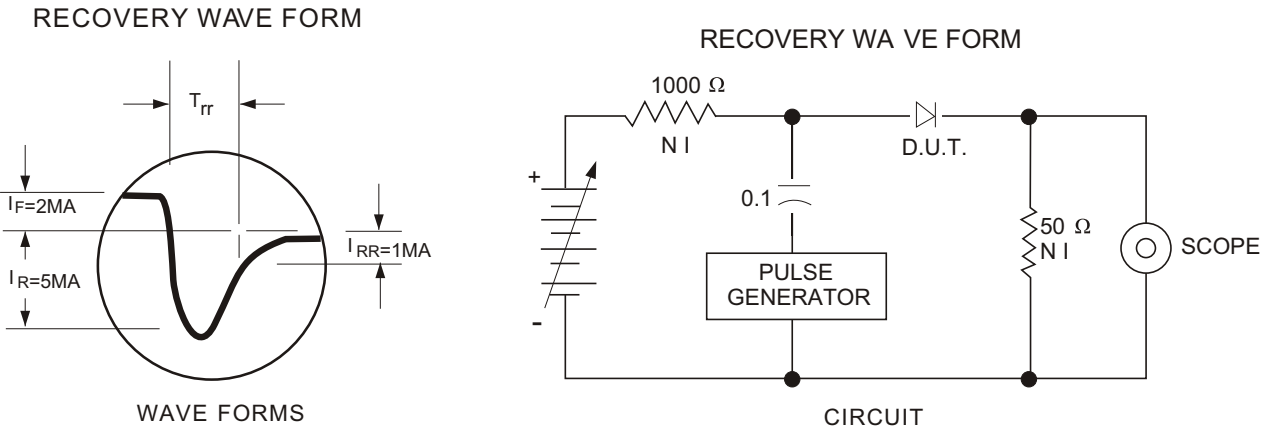


FIG.4

REVERSE RECOVERY TEST METHOD



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